IXYS

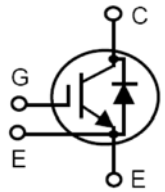
Preliminary Technical Information

XPT™ 650V GenX3™ w/ Sonic Diode

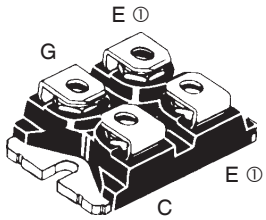
IXYN100N65C3H1

V_{CES} = 650V
I_{C110} = 90A
$V_{CE(sat)}$ ≤ 2.3V
$t_{fi(typ)}$ = 60ns

Extreme Light Punch Through
IGBT for 20-60kHz Switching



SOT-227B, miniBLOC
E153432



G = Gate, C = Collector, E = Emitter
① either emitter terminal can be used as Main or Kelvin Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 175°C	650	V
V_{CGR}	T_J = 25°C to 175°C, R_{GE} = 1MΩ	650	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	160	A
I_{C110}	T_C = 110°C	90	A
I_{F110}	T_C = 110°C	50	A
I_{CM}	T_C = 25°C, 1ms	420	A
I_A	T_C = 25°C	50	A
E_{AS}	T_C = 25°C	600	mJ
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 3Ω Clamped Inductive Load	I_{CM} = 200 $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	V_{GE} = 15V, V_{CE} = 360V, T_J = 150°C R_G = 10Ω, Non Repetitive	7	μs
P_C	T_C = 25°C	600	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
V_{ISOL}	50/60Hz t = 1min $I_{ISOL} \leq$ 1mA t = 1s	2500 3000	V~ V~
M_d	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in Nm/lb.in
Weight		30	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	650			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.5		6.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			50	μA
	T_J = 150°C			3	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 70A, V_{GE} = 15V, Note 1		1.8	2.3	V
	T_J = 150°C		2.2		V

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- 2500V~ Isolation Voltage
- Anti-Parallel Sonic Diode
- Optimized for 20-60kHz Switching
- Square RBSOA
- Short Circuit Capability
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- High Frequency Power Inverters

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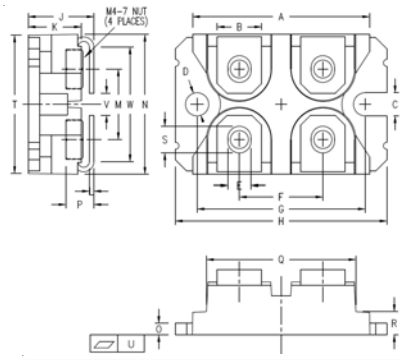
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	30	55		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		4800		pF
C_{oes}			475		pF
C_{res}			102		pF
$Q_{g(on)}$	I_C = 100A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		172		nC
Q_{ge}			30		nC
Q_{gc}			80		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		23		ns
t_{ri}	I_C = 50A, V_{GE} = 15V		42		ns
E_{on}	V_{CE} = 400V, R_G = 3Ω		1.30		mJ
$t_{d(off)}$	Note 2		107		ns
t_{fi}			60		ns
E_{off}			0.83	1.30	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		24		ns
t_{ri}	I_C = 50A, V_{GE} = 15V		38		ns
E_{on}	V_{CE} = 400V, R_G = 3Ω		2.55		mJ
$t_{d(off)}$	Note 2		134		ns
t_{fi}			66		ns
E_{off}			1.15		mJ
R_{thJC}				0.25	°C/W
R_{thCS}			0.05		°C/W

SOT-227B miniBLOC (IXYN)



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.489	1.505	37.80	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	−.002	.004	−0.05	0.1
V	.130	.180	3.30	4.57
W	.780	.830	19.81	21.08

Reverse Sonic Diode (FRD)

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 100A, V_{GE} = 0V, Note 1		1.7	2.3	V
	T_J = 150°C		1.8		V
I_{RM}	I_F = 100A, V_{GE} = 0V, T_J = 150°C,		95		A
t_{rr}	$-di_F/dt$ = 1500A/μs, V_R = 400V		100		ns
R_{thJC}				0.42	°C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

PRELIMANARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

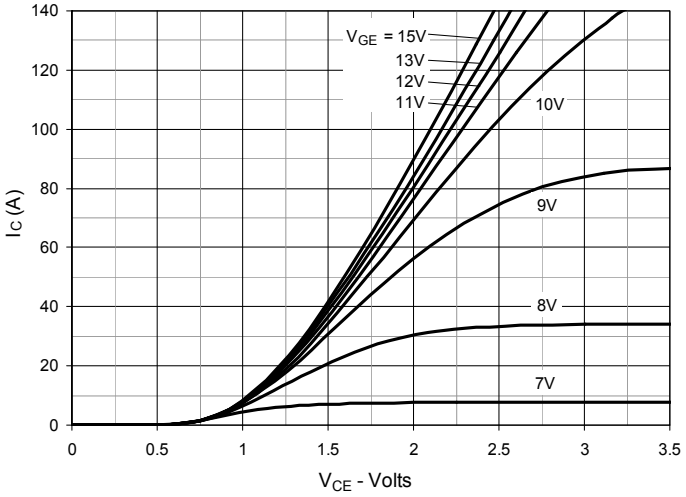


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

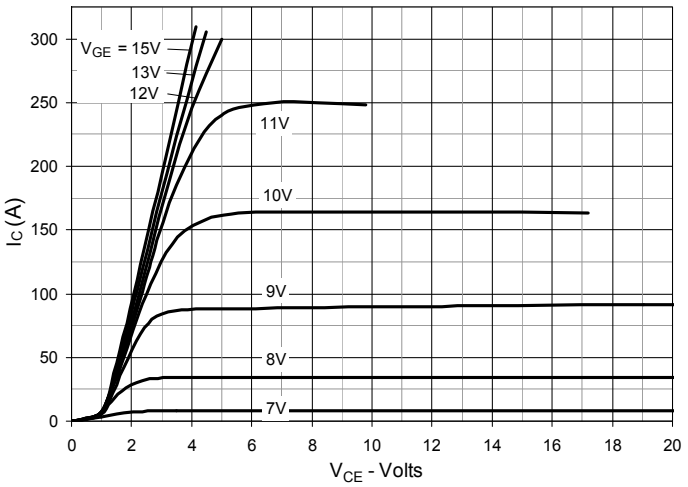


Fig. 3. Output Characteristics @ T_J = 150ºC

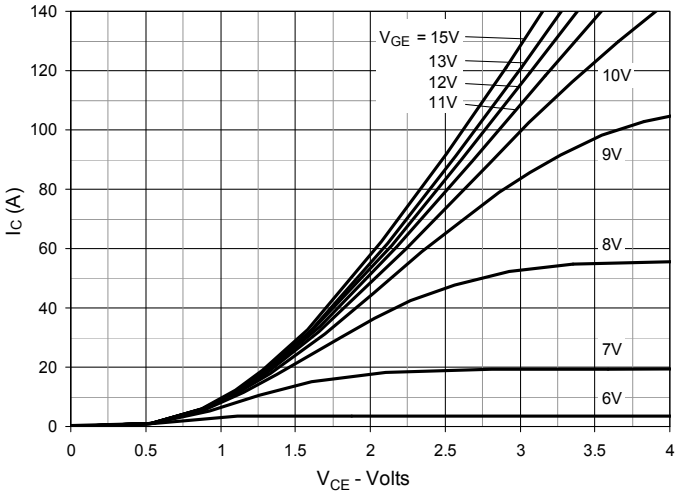


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

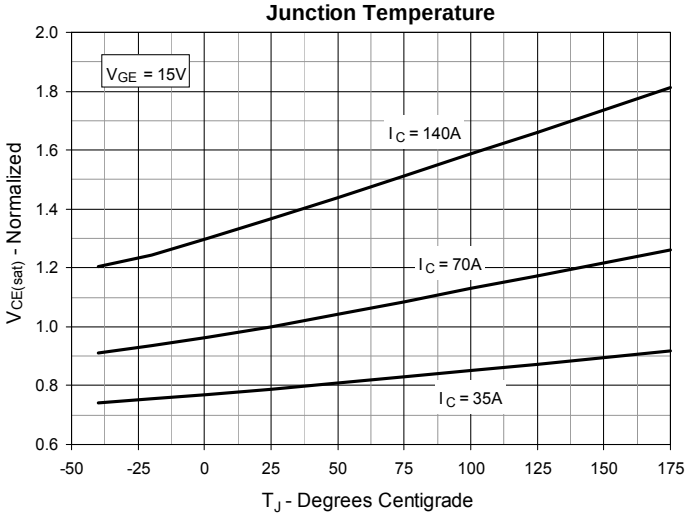


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

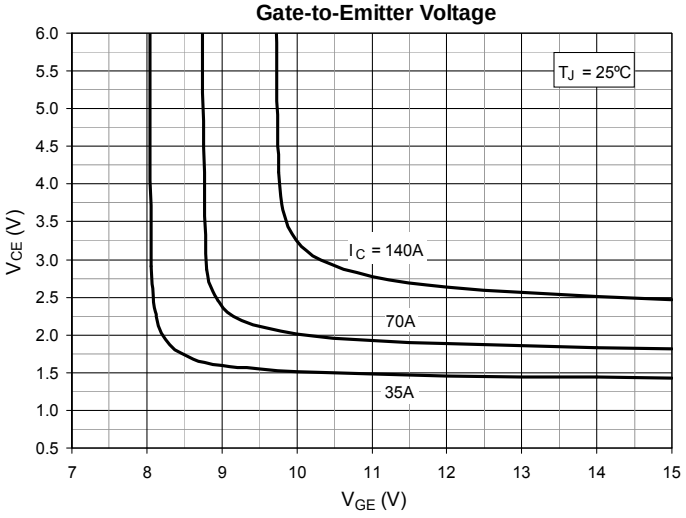


Fig. 6. Input Admittance

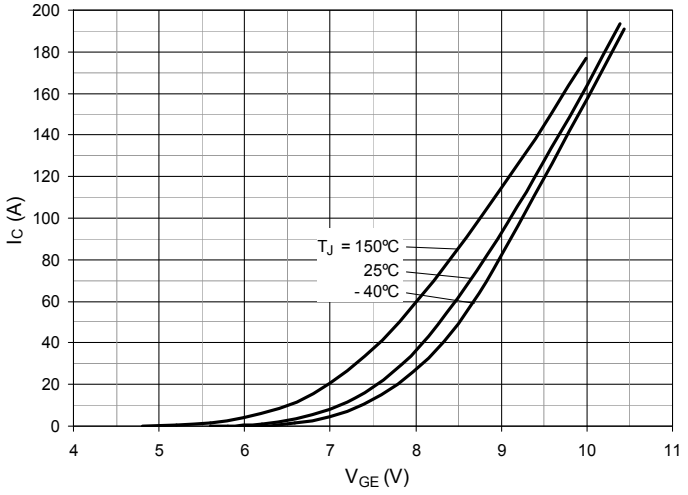


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Fig. 7. Transconductance

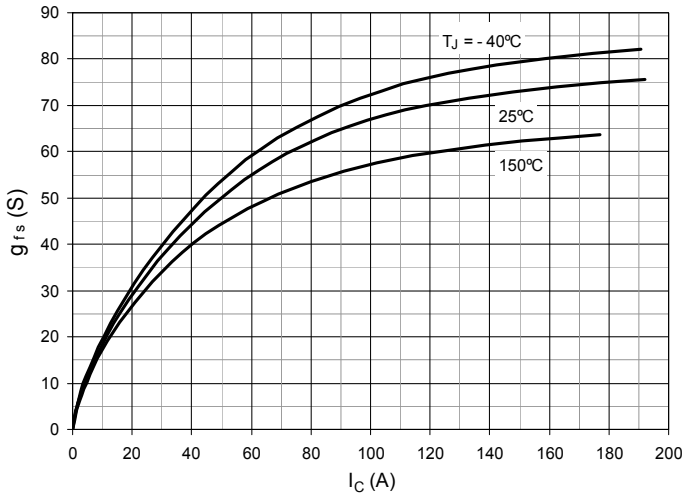


Fig. 8. Gate Charge

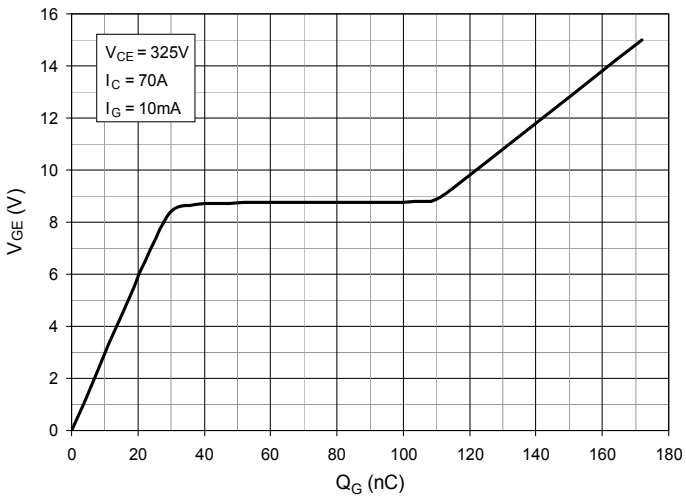


Fig. 9. Capacitance

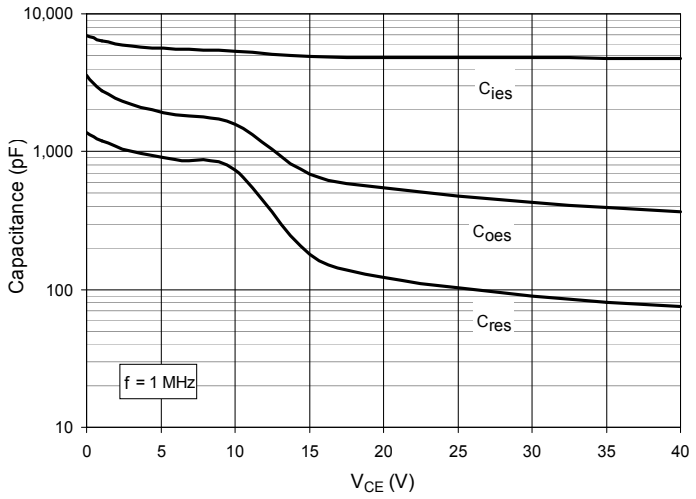


Fig. 10. Reverse-Bias Safe Operating Area

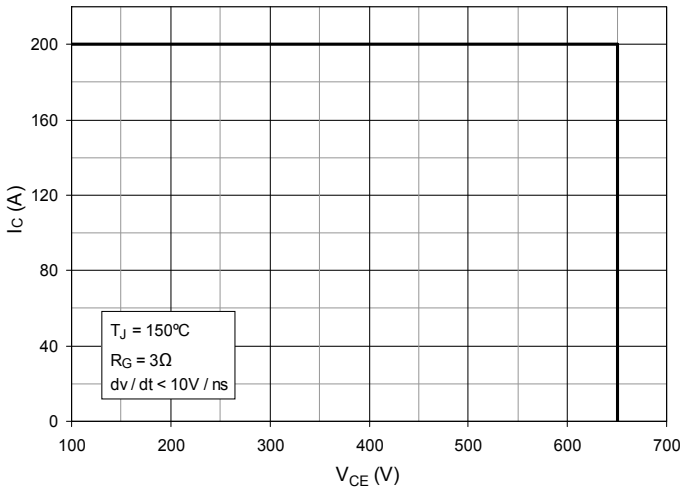


Fig. 11. Forward-Bias Safe Operating Area

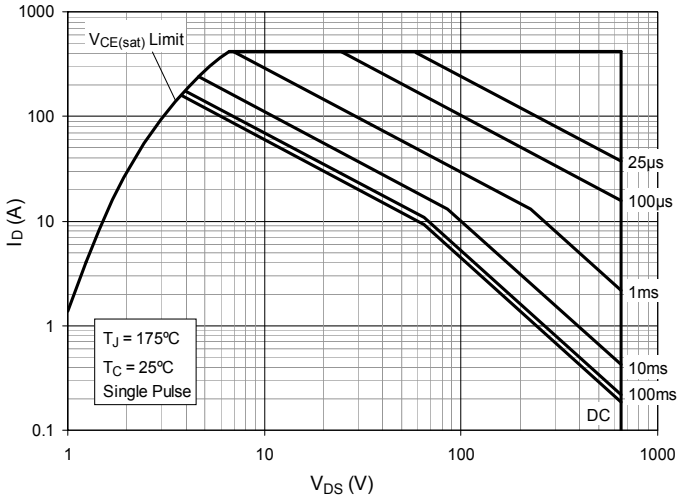
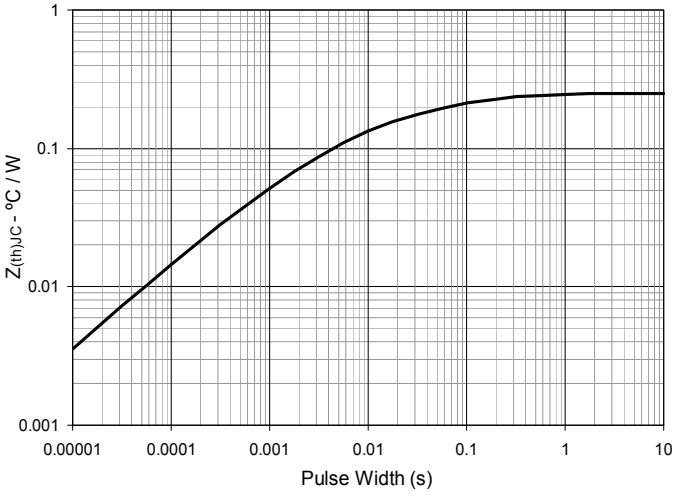


Fig. 12. Maximum Transient Thermal Impedance (IGBT)



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

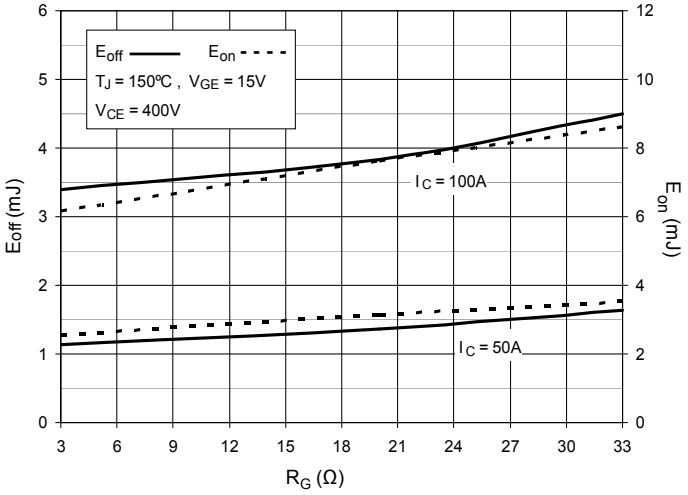


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

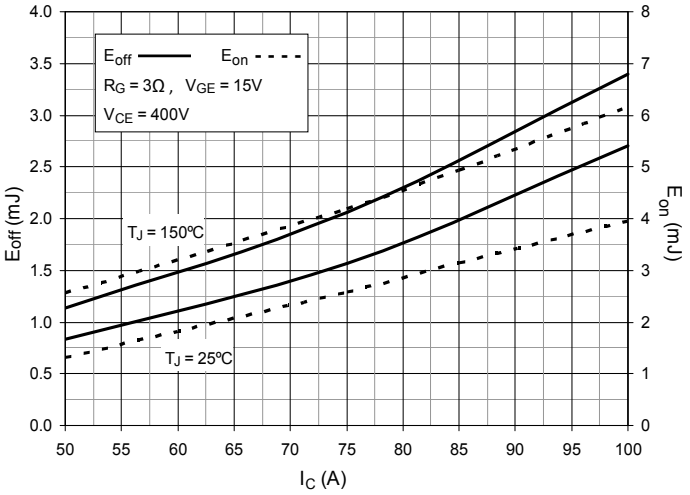


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

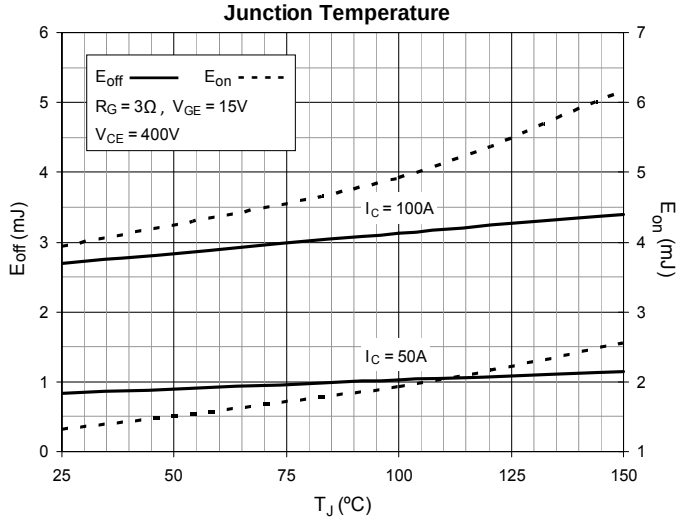


Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

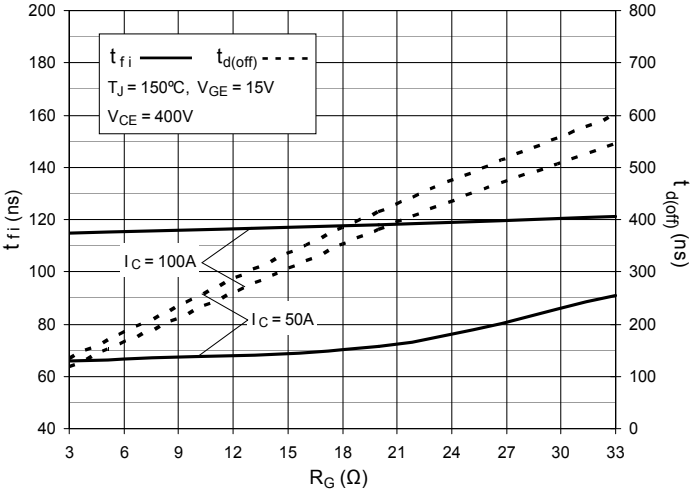


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

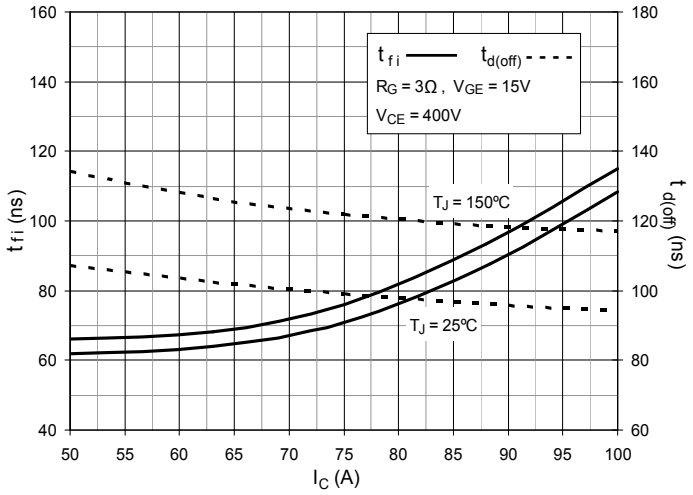


Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature

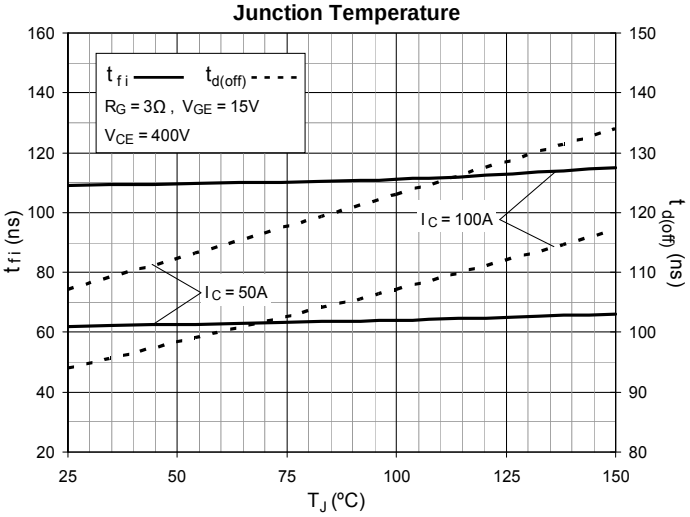


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Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

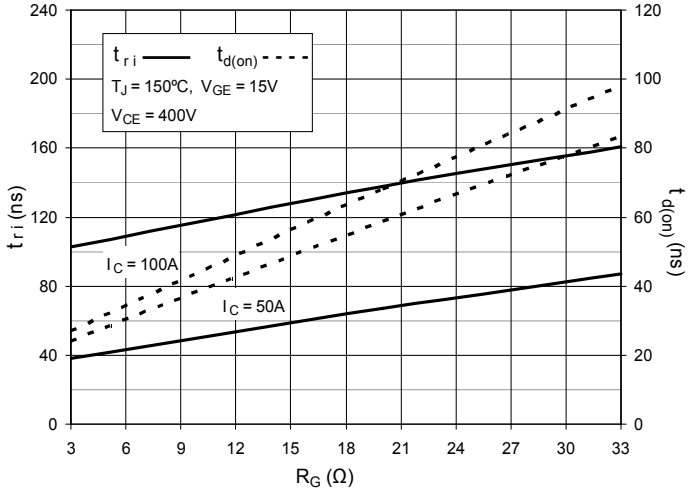


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

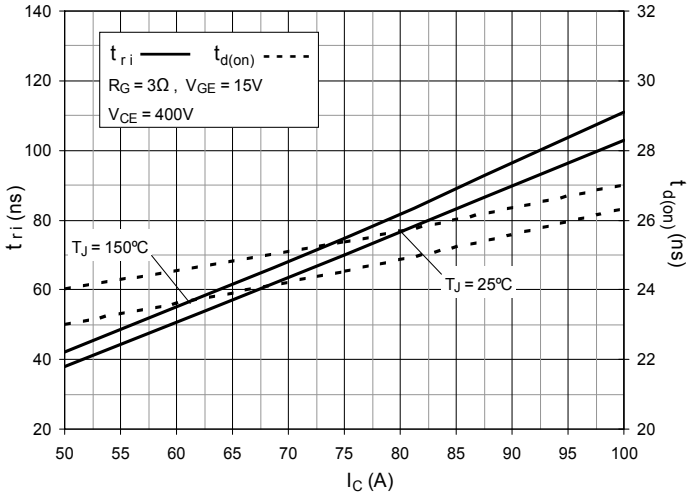


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature

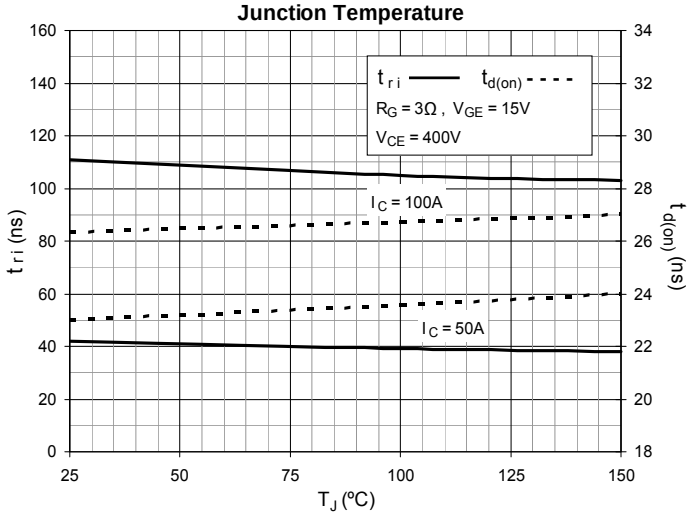


Fig. 22. Maximum Peak Load Current vs. Frequency

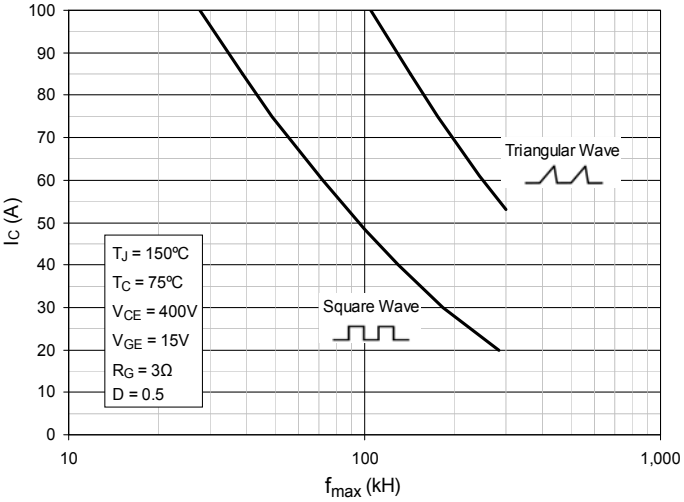


Fig. 23. Typ. Forward characteristics

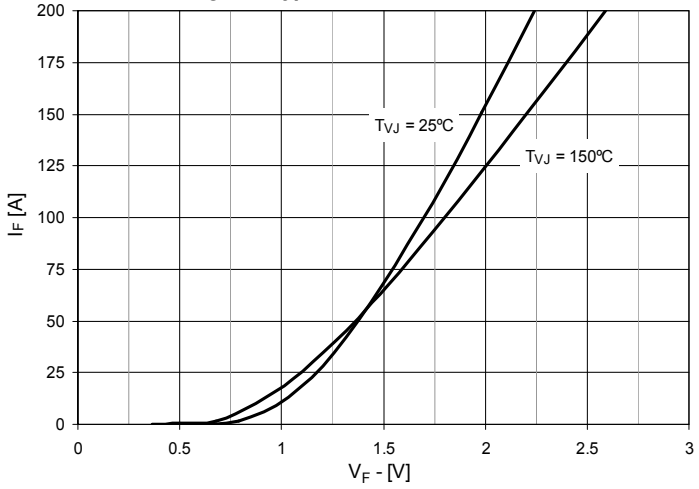


Fig. 24. Typ. Reverse Recovery Charge Q_{rr} vs. -di_F/dt

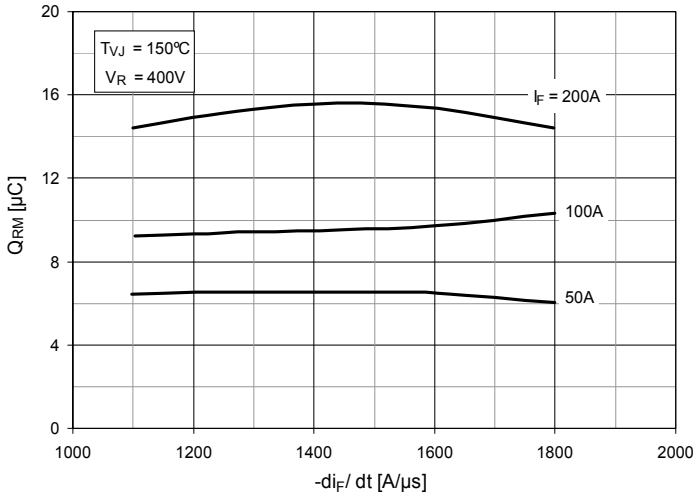


Fig. 25. Typ. Peak Reverse Current I_{RM} vs. -di_F/dt

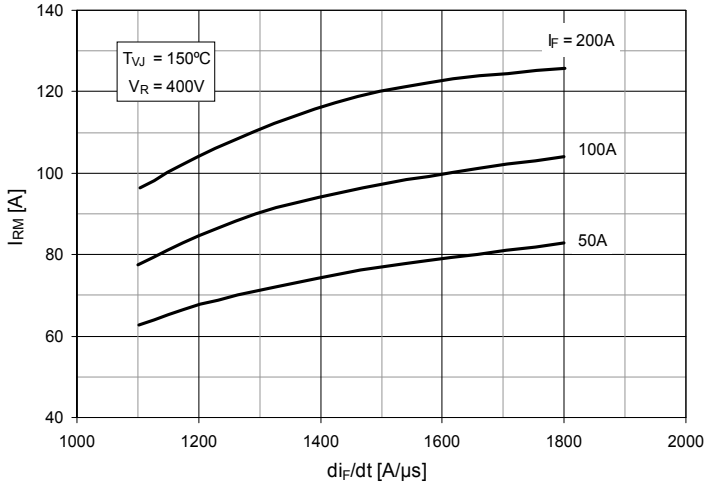


Fig. 26. Typ. Recovery Time t_{rr} vs. -di_F/dt

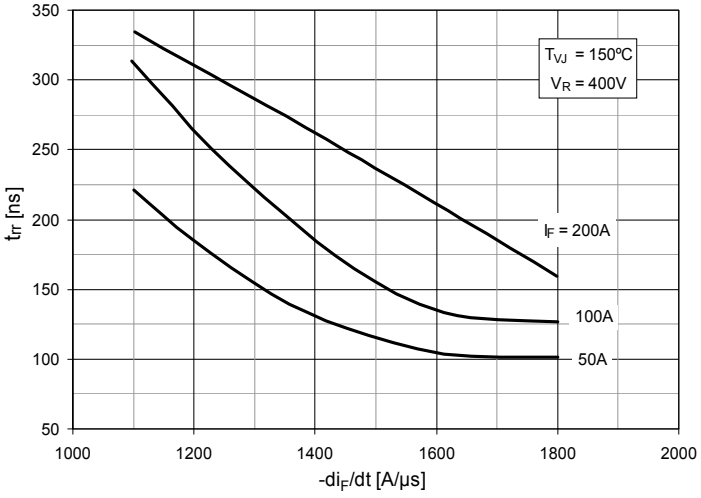


Fig. 27. Typ. Recovery Energy E_{rec} vs. -di_F/dt

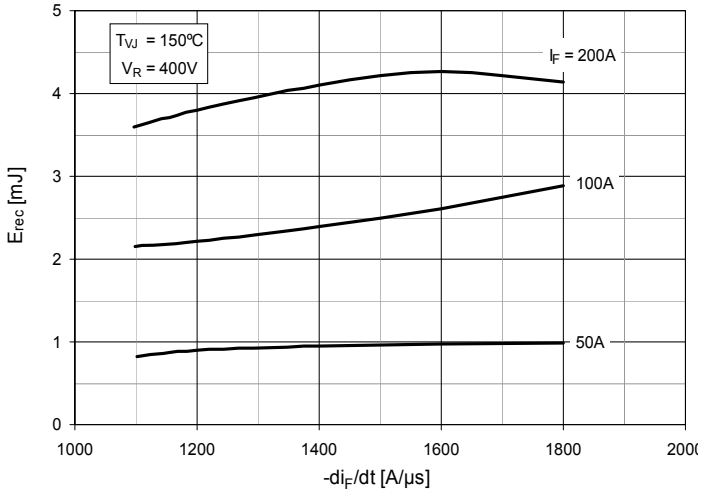
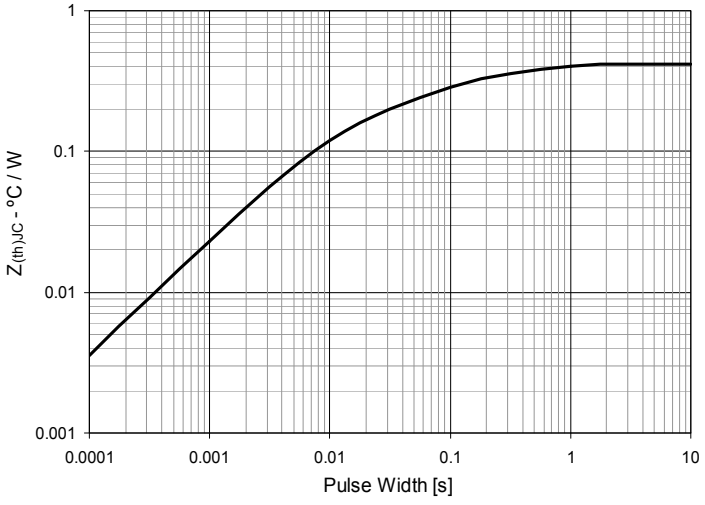


Fig. 28. Maximum Transient Thermal Impedance (Diode)



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